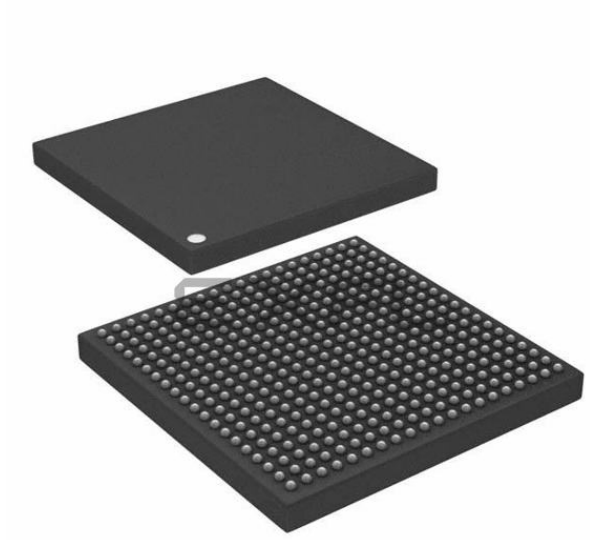

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Understanding Embedded - DSP (Digital Signal Processors)

Embedded - DSP (Digital Signal Processors) are specialized microprocessors designed to perform complex mathematical computations on digital signals in real-time. Unlike general-purpose processors, DSPs are optimized for high-speed numeric processing tasks, making them ideal for applications that require efficient and precise manipulation of digital data. These processors are fundamental in converting and processing signals in various forms, including audio, video, and communication signals, ensuring that data is accurately interpreted and utilized in embedded systems.

Applications of Embedded - DSP (Digital Signal Processors)

Details	
Product Status	Obsolete
Type	SC1400 Core
Interface	Host Interface, I²C, UART
Clock Rate	266MHz
Non-Volatile Memory	External
On-Chip RAM	208kB
Voltage - I/O	3.30V
Voltage - Core	1.20V
Operating Temperature	-40°C ~ 105°C (TJ)
Mounting Type	Surface Mount
Package / Case	400-LFBGA
Supplier Device Package	400-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/msc7112vf1000

1.2 Signal List By Ball Location

Table 1 lists the signals sorted by ball number and configuration.

Table 1. MSC7112 Signals by Ball Designator

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
A1	GND					
A2	GND					
A3	DQM1					
A4	DQS2					
A5	CK					
A6	$\overline{CK}$					
A7	GPIC7			GPOC7	HD15	
A8	GPIC4			GPOC4	HD12	
A9	GPIC2			GPOC2	HD10	
A10	reserved				HD7	
A11	reserved				HD6	
A12	reserved				HD4	
A13	reserved				HD1	
A14	reserved				HD0	
A15	GND					
A16 (1L44X)	NC					
A16 (1M88B)	BM3	GPID8		GPOD7	reserved	
A17	NC					
A18	NC					
A19	NC					
A20	NC					
B1	V_{DDM}					
B2	NC					
B3	$\overline{CS0}$					
B4	DQM2					
B5	DQS3					
B6	DQS0					
B7	CKE					
B8	$\overline{WE}$					
B9	GPIC6			GPOC6	HD14	
B10	GPIC3			GPOC3	HD11	
B11	GPIC0			GPOC0	HD8	
B12	reserved				HD5	
B13	reserved				HD2	
B14	NC					
B15 (1L44X)	NC					

Table 1. MSC7112 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
F11	V_{DDM}					
F12	GND					
F13	GND					
F14	GND					
F15	V_{DDIO}					
F16	V_{DDC}					
F17	V_{DDC}					
F18	NC					
F19	NC					
F20	NC					
G1	GND					
G2	D13					
G3	GND					
G4	V_{DDM}					
G5	V_{DDM}					
G6	GND					
G7	GND					
G8	GND					
G9	GND					
G10	GND					
G11	GND					
G12	GND					
G13	GND					
G14	GND					
G15	V_{DDIO}					
G16	V_{DDIO}					
G17	V_{DDC}					
G18	NC					
G19	NC					
G20	NC					
H1	D14					
H2	D12					
H3	D11					
H4	V_{DDM}					
H5	V_{DDM}					
H6	GND					
H7	GND					
H8	GND					

Table 1. MSC7112 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
H9	GND					
H10	GND					
H11	GND					
H12	GND					
H13	GND					
H14	GND					
H15	V_{DDIO}					
H16	V_{DDIO}					
H17	V_{DDC}					
H18	NC					
H19	reserved				HA2	
H20	reserved				HA1	
J1	D10					
J2	V_{DDM}					
J3	D9					
J4	V_{DDM}					
J5	V_{DDM}					
J6	V_{DDM}					
J7	GND					
J8	GND					
J9	GND					
J10	GND					
J11	GND					
J12	GND					
J13	GND					
J14	GND					
J15	GND					
J16	V_{DDIO}					
J17	V_{DDC}					
J18 (1L44X)	reserved				HA3	
J18 (1M88B)	GPIC11			GPOC11	HA3	
J19	reserved				$\overline{\text{HACK}}$/HACK or $\overline{\text{HRRQ}}$/HRRQ	
J20	HDSP	reserved			$\overline{\text{HREQ}}$/HREQ or $\overline{\text{HTRQ}}$/HTRQ	
K1	D0					
K2	GND					
K3	D8					
K4	V_{DDC}					
K5	V_{DDM}					

2.5.2.1 PLL Multiplier Restrictions

There are two restrictions for correct usage of the PLL block:

- The input frequency to the PLL multiplier block (that is, the output of the divider) must be in the range 10.5–19.5 MHz.
- The output frequency of the PLL multiplier must be in the range 300-600 MHz.

When programming the PLL for a desired output frequency using the PLLDVF, PLLMLTF, and RNG fields, you must meet these constraints.

2.5.2.2 Division Factors and Corresponding CLKIN Frequency Range

The value of the PLLDVF field determines the allowable CLKIN frequency range, as shown in **Table 10**.

Table 10. CLKIN Frequency Ranges by Divide Factor Value

PLLDVF Field Value	Divide Factor	CLKIN Frequency Range	Comments
0x00	1	10.5 to 19.5 MHz	Pre-Division by 1
0x01	2	21 to 39 MHz	Pre-Division by 2
0x02	3	31.5 to 58.5 MHz	Pre-Division by 3
0x03	4	42 to 78 MHz	Pre-Division by 4
0x04	5	52.5 to 97.5 MHz	Pre-Division by 5
0x05	6	63 to 100 MHz	Pre-Division by 6
0x06	7	73.5 to 100 MHz	Pre-Division by 7
0x07	8	84 to 100 MHz	Pre-Division by 8
0x08	9	94.5 to 100 MHz	Pre-Division by 9
Note: The maximum CLKIN frequency is 100 MHz. Therefore, the PLLDVF value must be in the range from 1–9.			

2.5.2.3 Multiplication Factor Range

The multiplier block output frequency ranges depend on the input clock frequency as shown in **Table 11**.

Table 11. PLLMLTF Ranges

Multiplier Block (Loop) Output Range	Minimum PLLMLTF Value	Maximum PLLMLTF Value
300 ≤ [Pre-Divided Clock × (PLLMLTF + 1)] ≤ 600 MHz	300/Pre-Divided Clock	600/Pre-Divided Clock
Note: This table results from the allowed range for F_{Loop}. The minimum and maximum multiplication factors are dependent on the frequency of the Pre-Divided Clock.		

2.5.2.4 Allowed Core Clock Frequency Range

The frequency delivered to the core, extended core, and peripheral depends on the value of the CLKCTRL[RNG] bit as shown in **Table 12**.

Table 12. F_{vco} Frequency Ranges

CLKCTRL[RNG] Value	Allowed Range of F_{vco}
1	$300 \le F_{vco} \le 600$ MHz
0	$150 \le F_{vco} \le 300$ MHz
Note: This table results from the allowed range for F_{vco}, which is F_{Loop} modified by CLKCTRL[RNG].	

This bit along with the CKSEL determines the frequency range of the core clock.

Figure 6 shows the DDR DRAM output timing diagram.

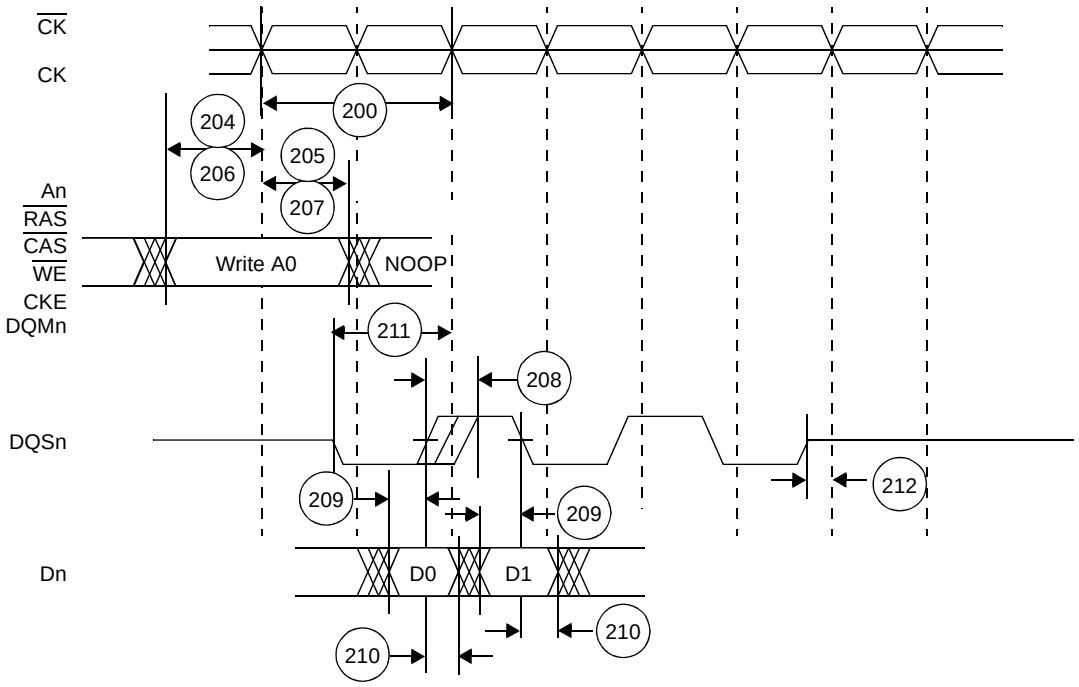

Figure 6. DDR DRAM Output Timing Diagram

Figure 7 provides the AC test load for the DDR DRAM bus.

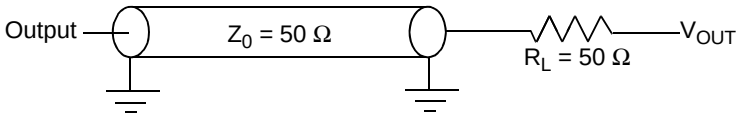

Figure 7. DDR DRAM AC Test Load

Table 20. DDR DRAM Measurement Conditions

Symbol	DDR DRAM	Unit
V_{TH}[1]	V_{REF} ± 0.31 V	V
V_{OUT}[2]	0.5 × V_{DDM}	V

Notes: **1.** Data input threshold measurement point.
2. Data output measurement point.

2.5.5 TDM Timing

Table 21. TDM Timing

No.	Characteristic	Expression	Min	Max	Units
300	TDMxRCK/TDMxTCK	TC	20.0	—	ns
301	TDMxRCK/TDMxTCK High Pulse Width	0.4 × TC	8.0	—	ns
302	TDMxRCK/TDMxTCK Low Pulse Width	0.4 × TC	8.0	—	ns
303	TDM all input Setup time		3.0	—	ns
304	TDMxRD Hold time		3.5	—	ns
305	TDMxTFS/TDMxRFS input Hold time		2.0	—	ns
306	TDMxTCK High to TDMxTD output active		4.0	—	ns

2.5.6 HDI16 Signals

Table 22. Host Interface (HDI16) Timing[1, 2]

No.	Characteristics[3]	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	
40	Host Interface Clock period	T_{HCLK}	Note 1	T_{CORE}	Note 1	ns
44a	Read data strobe minimum assertion width[4] HACK read minimum assertion width	$3.0 \times T_{HCLK}$	Note 11	$2.0 \times T_{CORE} + 9.0$	Note 11	ns
44b	Read data strobe minimum deassertion width[4] HACK read minimum deassertion width	$1.5 \times T_{HCLK}$	Note 11	$1.5 \times T_{CORE}$	Note 11	ns
44c	Read data strobe minimum deassertion width[4] after “Last Data Register” reads[5,6], or between two consecutive CVR, ICR, or ISR reads[7] HACK minimum deassertion width after “Last Data Register” reads[5,6]	$2.5 \times T_{HCLK}$	Note 11	$2.5 \times T_{CORE}$	Note 11	ns
45	Write data strobe minimum assertion width[8] HACK write minimum assertion width	$1.5 \times T_{HCLK}$	Note 11	$1.5 \times T_{CORE}$	Note 11	ns
46	Write data strobe minimum deassertion width[8] HACK write minimum deassertion width after ICR, CVR and Data Register writes[5]	$2.5 \times T_{HCLK}$	Note 11	$2.5 \times T_{CORE}$	Note 11	ns
47	Host data input minimum setup time before write data strobe deassertion[8] Host data input minimum setup time before HACK write deassertion	—	3.0	—	2.5	ns
48	Host data input minimum hold time after write data strobe deassertion[8] Host data input minimum hold time after HACK write deassertion	—	4.0	—	2.5	ns
49	Read data strobe minimum assertion to output data active from high impedance[4] HACK read minimum assertion to output data active from high impedance	—	1.0	—	1.0	ns
50	Read data strobe maximum assertion to output data valid[4] HACK read maximum assertion to output data valid	$(2.0 \times T_{HCLK}) + 8.0$	Note 11	$(2.0 \times T_{CORE}) + 8.0$	Note 11	ns
51	Read data strobe maximum deassertion to output data high impedance[4] HACK read maximum deassertion to output data high impedance	—	8.0	—	9.0	ns
52	Output data minimum hold time after read data strobe deassertion[4] Output data minimum hold time after HACK read deassertion	—	1.0	—	1.0	ns
53	HCS[1–2] minimum assertion to read data strobe assertion[4]	—	0.0	—	0.5	ns
54	HCS[1–2] minimum assertion to write data strobe assertion[8]	—	0.0	—	0.0	ns
55	HCS[1–2] maximum assertion to output data valid	$(2.0 \times T_{HCLK}) + 8.0$	Note 11	$(2.0 \times T_{CORE}) + 6.0$	Note 11	ns
56	HCS[1–2] minimum hold time after data strobe deassertion[9]	—	0.0	—	0.5	ns
57	HA[0–3], HRW minimum setup time before data strobe assertion[9]	—	5.0	—	5.0	ns
58	HA[0–3], HRW minimum hold time after data strobe deassertion[9]	—	5.0	—	5.0	ns
61	Maximum delay from read data strobe deassertion to host request deassertion for “Last Data Register” read[4, 5, 10]	$(3.0 \times T_{HCLK}) + 8.0$	Note 11	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
62	Maximum delay from write data strobe deassertion to host request deassertion for “Last Data Register” write[5,8,10]	$(3.0 \times T_{HCLK}) + 8.0$	Note 11	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
63	Minimum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) deassertion to HREQ assertion.	$(2.0 \times T_{HCLK}) + 1.0$	Note 11	$(2.0 \times T_{CORE}) + 1.0$	Note 11	ns
64	Maximum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) assertion to HREQ deassertion	$(5.0 \times T_{HCLK}) + 8.0$	Note 11	$(5.0 \times T_{CORE}) + 6.0$	Note 11	ns

Table 22. Host Interface (HDI16) Timing[1, 2] (continued)

No.	Characteristics[3]	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	

Notes:
1. T_{HCLK} = 2/ (Core Clock). At 200 MHz, T_{HCLK} = 10 ns. T_{CORE} = core clock period. At 266 MHz, T_{CORE} = 3.75 ns.
2. In the timing diagrams below, the controls pins are drawn as active low. The pin polarity is programmable.
3. V_{DD} = 3.3 V ± 0.15 V; T_J = –40°C to +105 °C, C_L = 30 pF for maximum delay timings and C_L = 0 pF for minimum delay timings.
4. The read data strobe is HRD/HRD in the dual data strobe mode and HDS/HDS in the single data strobe mode.
5. For 64-bit transfers, The “last data register” is the register at address 0x7, which is the last location to be read or written in data transfers. This is RX0/TX0 in the little endian mode (HBE = 0), or RX3/TX3 in the big endian mode (HBE = 1).
6. This timing is applicable only if a read from the “last data register” is followed by a read from the RXL, RXM, or RXH registers without first polling RXDF or HREQ bits, or waiting for the assertion of the HREQ/HREQ signal.
7. This timing is applicable only if two consecutive reads from one of these registers are executed.
8. The write data strobe is HWR in the dual data strobe mode and HDS in the single data strobe mode.
9. The data strobe is host read (HRD/HRD) or host write (HWR/HWR) in the dual data strobe mode and host data strobe (HDS/HDS) in the single data strobe mode.
10. The host request is HREQ/HREQ in the single host request mode and HRRQ/HRRQ and HTRQ/HTRQ in the double host request mode. HRRQ/HRRQ is deasserted only when HOTX fifo is empty, HTRQ/HTRQ is deasserted only if HORX fifo is full (treat as level Host Request).
11. Compute the value using the expression.
12. For mask set 1M88B, the read and write data strobe minimum deassertion width for non-”last data register” accesses in single and dual data strobe modes is based on timings 57 and 58.

Figure 10 and **Figure 11** show HDI16 read signal timing. **Figure 12** and **Figure 13** show HDI16 write signal timing.

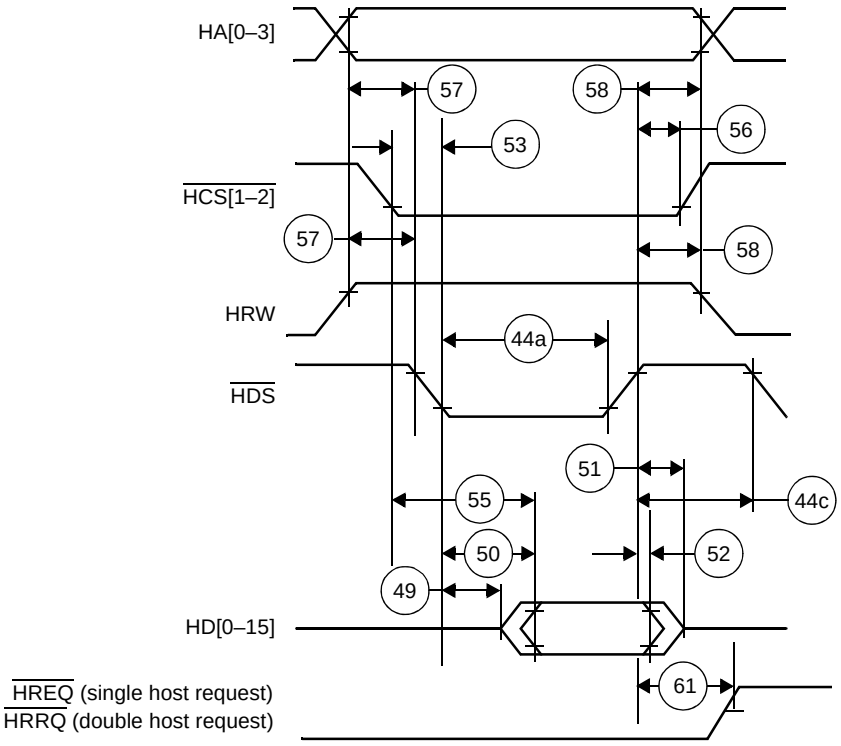

Figure 10. Read Timing Diagram, Single Data Strobe

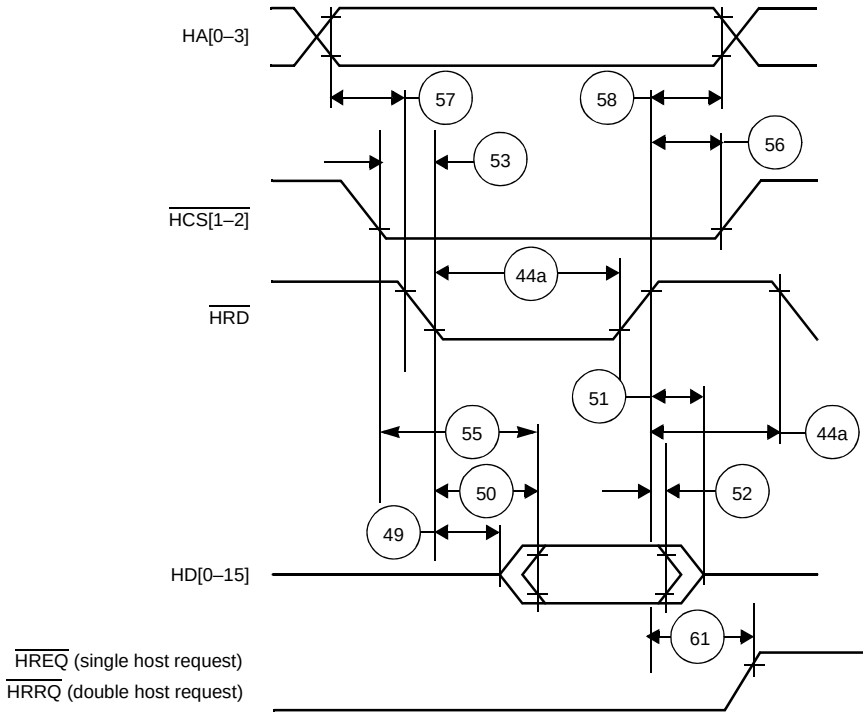

Figure 11. Read Timing Diagram, Double Data Strobe

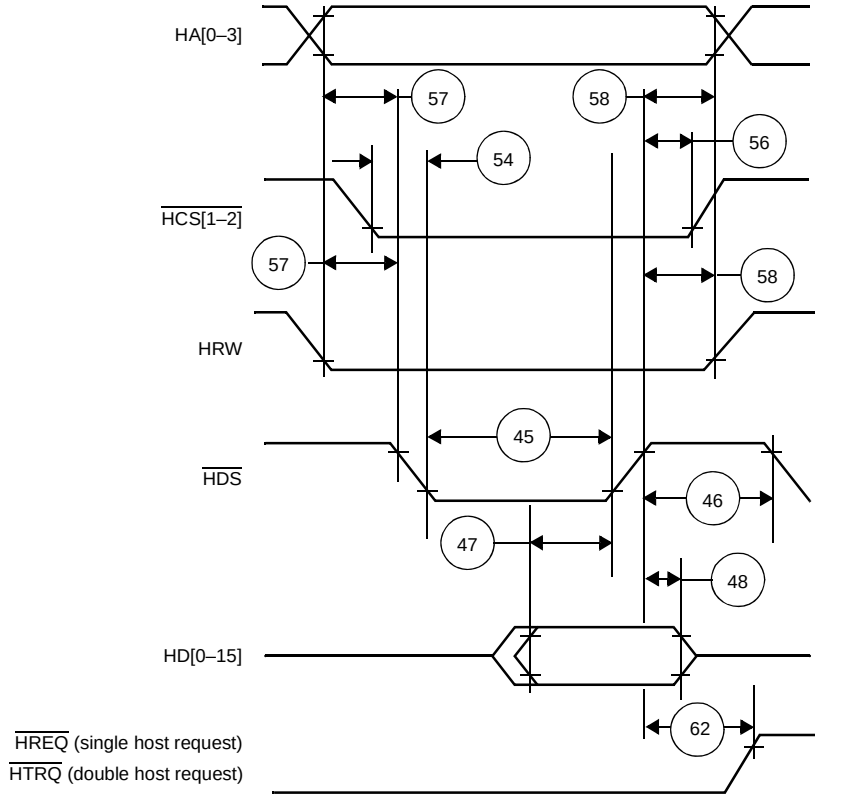

Figure 12. Write Timing Diagram, Single Data Strobe

2.5.8 UART Timing

Table 24. UART Timing

No.	Characteristics	Expression	Mask Set 1L44X		Mask Set 1M88B		Unit
			Min	Max	Min	Max	
—	Internal bus clock (APBCLK)	$F_{CORE}/2$	—	100	—	133	MHz
—	Internal bus clock period (1/APBCLK)	T_{APBCLK}	10.0	—	7.52	—	ns
400	URXD and UTXD inputs high/low duration	$16 \times T_{APBCLK}$	160.0	—	120.3	—	ns
401	URXD and UTXD inputs rise/fall time		—	5	—	5	ns
402	UTXD output rise/fall time		—	5	—	5	ns

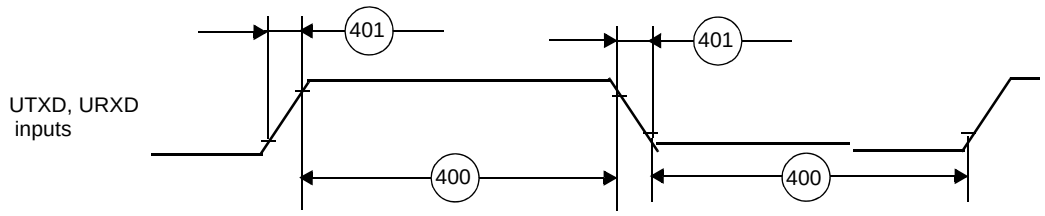

Figure 17. UART Input Timing

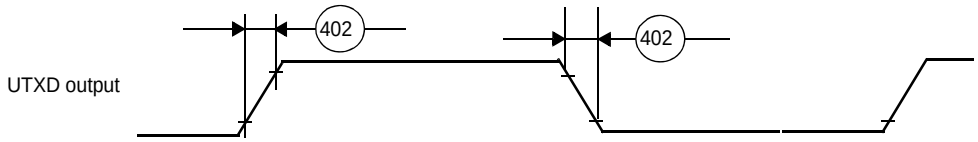

Figure 18. UART Output Timing

2.5.9 EE Timing

Table 25. EE0 Timing

Number	Characteristics	Type	Min
65	EE0 input to the core	Asynchronous	4 core clock periods
66	EE0 output from the core	Synchronous to core clock	1 core clock period

Notes:
1. The core clock is the SC1400 core clock. The ratio between the core clock and CLKOUT is configured during power-on-reset.
2. Configure the direction of the EE pin in the EE_CTRL register (see the *SC1400 Core Reference Manual* for details.
3. Refer to **Table 15** for details on EE pin functionality.

Figure 19 shows the signal behavior of the EE pin.

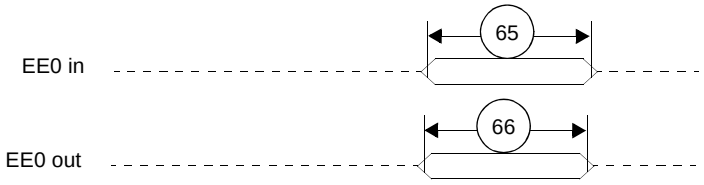

Figure 19. EE Pin Timing

2.5.10 Event Timing

Table 26. EVNT Signal Timing

Number	Characteristics	Type	Min
67	EVNT as input	Asynchronous	1.5 × APBCLK periods
68	EVNT as output	Synchronous to core clock	1 APBCLK period

Notes:
1. Refer to **Table 24** for a definition of the APBCLK period.
2. Direction of the EVNT signal is configured through the GPIO and Event port registers.
3. Refer to the *MSC711x Reference Manual* for details on EVNT pin functionality.

Figure 20 shows the signal behavior of the EVNT pin.

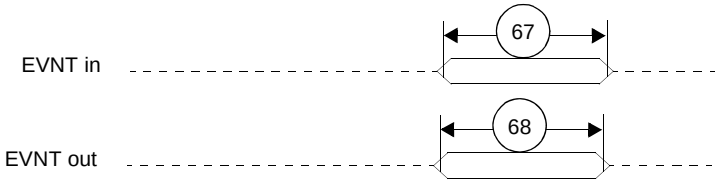

Figure 20. EVNT Pin Timing

2.5.11 GPIO Timing

Table 27. GPIO Signal Timing[1,2,3]

Number	Characteristics	Type	Min
601	GPI[4,5]	Asynchronous	1.5 × APBCLK periods
602	GPO[5]	Synchronous to core clock	1 APBCLK period
603	Port A edge-sensitive interrupt	Asynchronous	1.5 × APBCLK periods
604	Port A level-sensitive interrupt	Asynchronous	3 × APBCLK periods[6]

Notes:
1. Refer to **Table 24** for a definition of the APBCLK period.
2. Direction of the GPIO signal is configured through the GPIO port registers.
3. Refer to *MSC711x Reference Manual* for details on GPIO pin functionality.
4. GPI data is synchronized to the APBCLK internally and the minimum listed is the capability of the hardware to capture data into a register when the GPA_DR is read. The specification is not tested due to the asynchronous nature of the input and dependence on the state of the DSP core. It is guaranteed by design.
5. The input and output signals cannot toggle faster than 50 MHz.
6. Level-sensitive interrupts should be held low until the system determines (via the service routine) that the interrupt is acknowledged.

Figure 21 shows the signal behavior of the GPI/GPO pin.

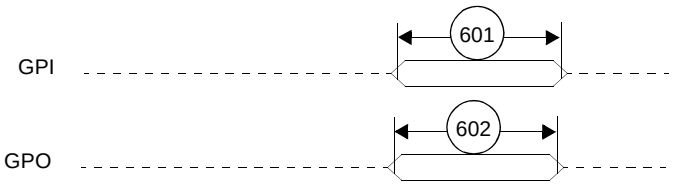

Figure 21. GPI/GPO Pin Timing

3.2 Power Supply Design Considerations

This section outlines the MSC7112 power considerations: power supply, power sequencing, power planes, decoupling, power supply filtering, and power consumption. It also presents a recommended power supply design and options for low-power consumption. For information on AC/DC electrical specifications and thermal characteristics, refer to **Section 2**.

3.2.1 Power Supply

The MSC7112 requires four input voltages, as shown in **Table 29**.

Table 29. MSC7112 Voltages

Voltage	Symbol	Value
Core	V_{DDC}	1.2 V
Memory	V_{DDM}	2.5 V
Reference	V_{REF}	1.25 V
I/O	V_{DDIO}	3.3 V

You should supply the MSC7112 core voltage via a variable switching supply or regulator to allow for compatibility with possible core voltage changes on future silicon revisions. The core voltage is supplied with 1.2 V (+5% and –10%) across V_{DDC} and GND and the I/O section is supplied with 3.3 V (± 10%) across V_{DDIO} and GND. The memory and reference voltages supply the DDR memory controller block. The memory voltage is supplied with 2.5 V across V_{DDM} and GND. The reference voltage is supplied across V_{REF} and GND and must be between $0.49 \times V_{DDM}$ and $0.51 \times V_{DDM}$. Refer to the JEDEC standard JESD8 (*Stub Series Terminated Logic for 2.5 Volts* (STTL_2)) for memory voltage supply requirements.

3.2.2 Power Sequencing

One consequence of multiple power supplies is that the voltage rails ramp up at different rates when power is initially applied. The rates depend on the power supply, the type of load on each power supply, and the way different voltages are derived. It is extremely important to observe the power up and power down sequences at the board level to avoid latch-up, forward biasing of ESD devices, and excessive currents, which all lead to severe device damage.

Note: There are five possible power-up/power-down sequence cases. The first four cases listed in the following sections are recommended for new designs. The fifth case is not recommended for new designs and must be carefully evaluated for current spike risks based on actual information for the specific application.

3.2.2.1 Case 1

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) supply second.
3. Turn on the V_{DDM} (2.5 V) supply third.
4. Turn on the V_{REF} (1.25 V) supply fourth (last).

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 26** for relative timing for power sequencing case 1.

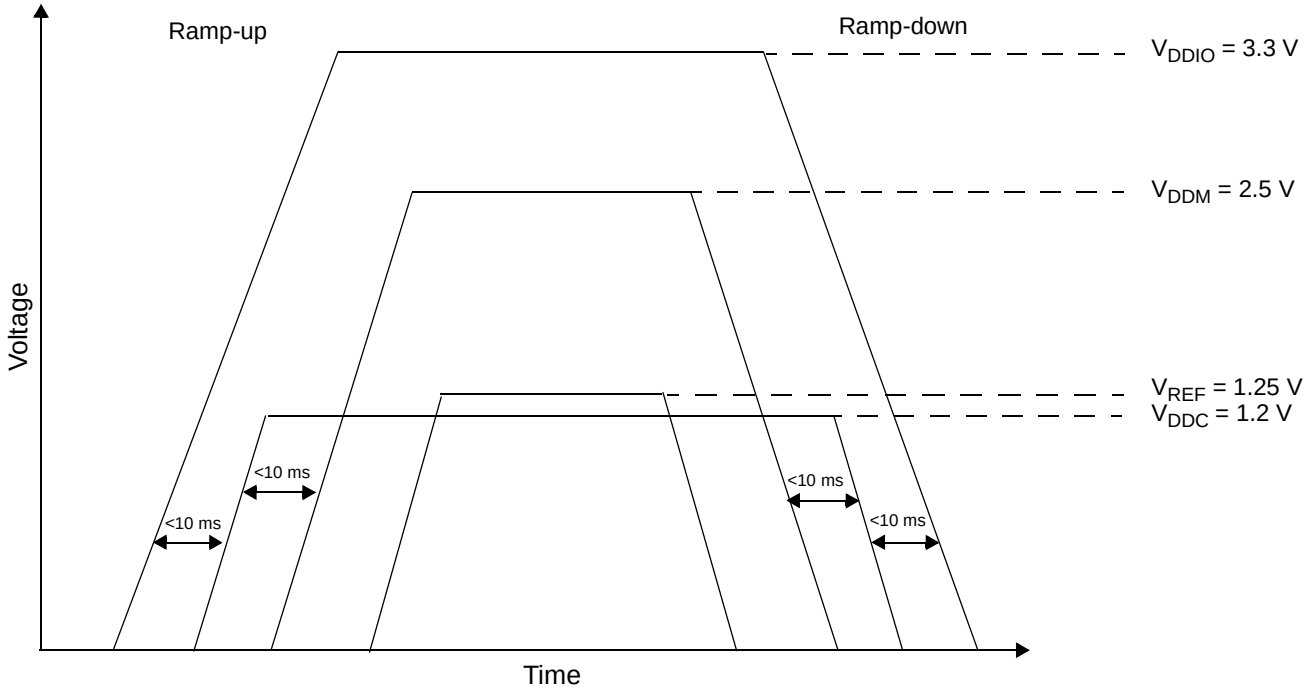

Figure 26. Voltage Sequencing Case 1

3.2.2.2 Case 2

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) and V_{DDM} (2.5 V) supplies simultaneously (second).
3. Turn on the V_{REF} (1.25 V) supply last (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC}/V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 27** for relative timing for Case 2.

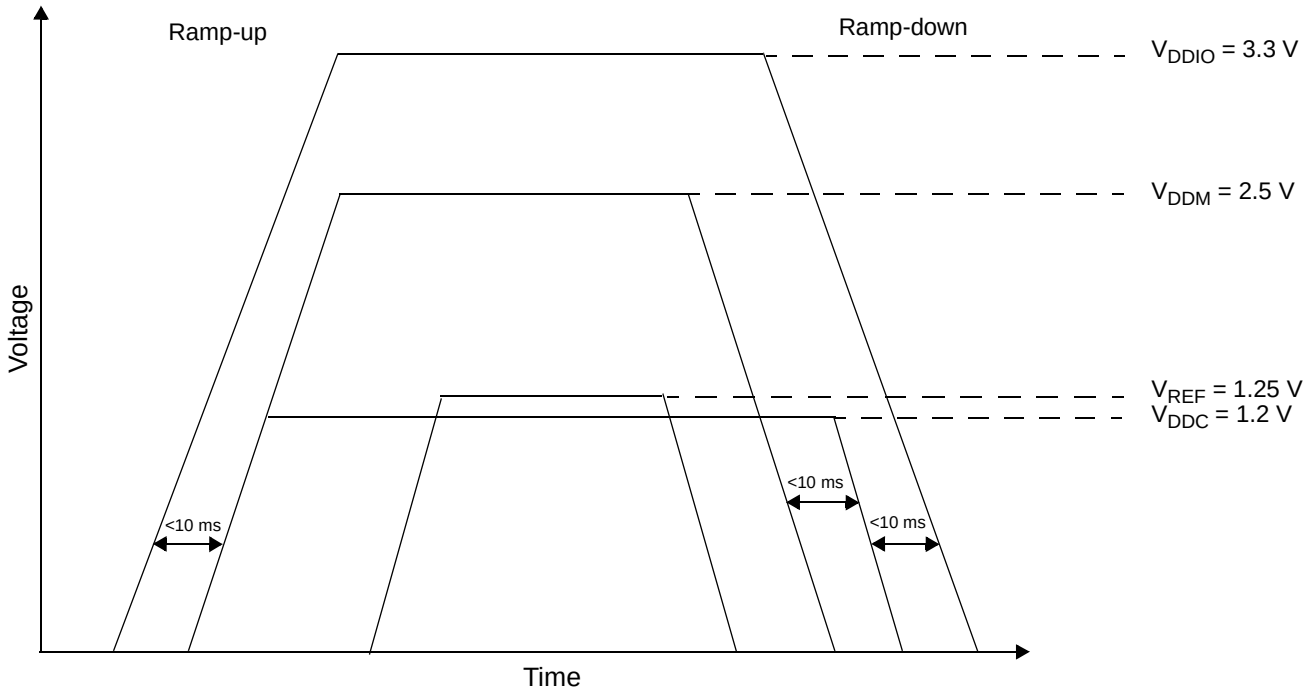

Figure 27. Voltage Sequencing Case 2

3.2.2.4 Case 4

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V), V_{DDM} (2.5 V), and V_{REF} (1.25 V) supplies simultaneously (second).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{DDC} (1.2 V), V_{REF} (1.25 V), and V_{DDM} (2.5 V) supplies simultaneously (first).
2. Turn of the V_{DDIO} (3.3 V) supply last.

Use the following guidelines:

- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 29** for relative timing for Case 4.

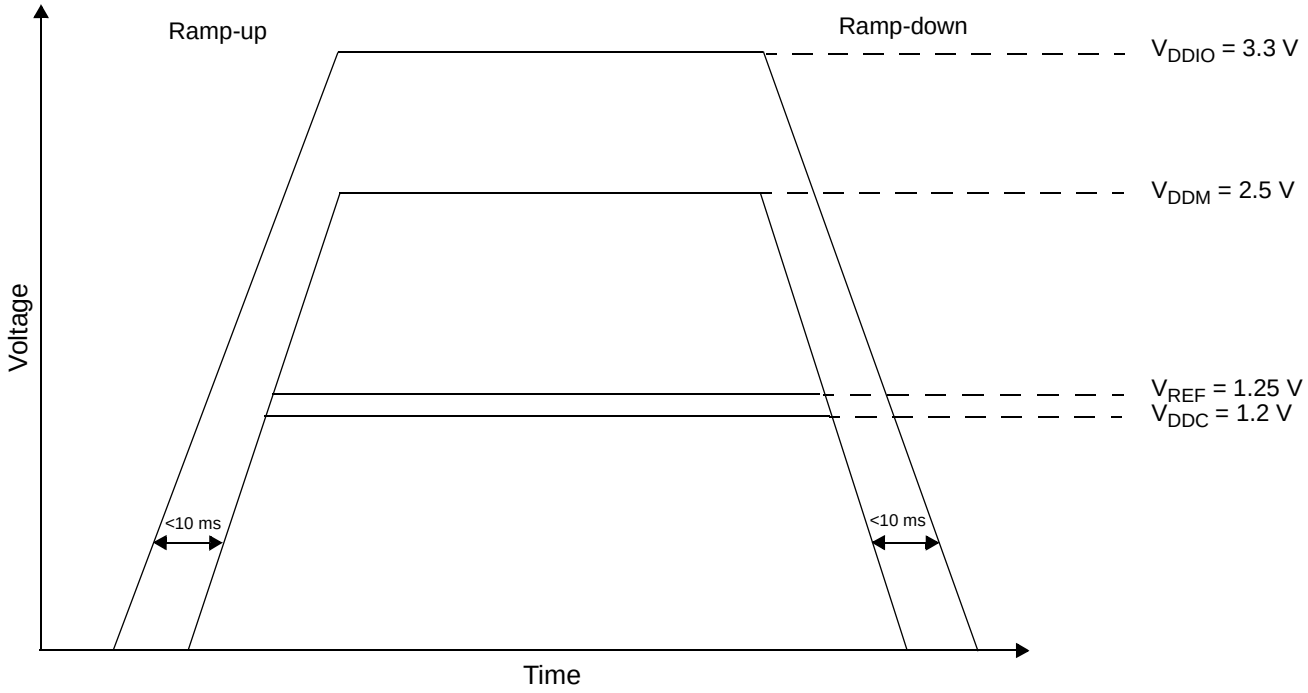

Figure 29. Voltage Sequencing Case 4

3.2.2.5 Case 5 (not recommended for new designs)

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDM} (2.5 V) supply second.
3. Turn on the V_{DDC} (1.2 V) supply third.
4. Turn on the V_{REF} (1.25 V) supply fourth (last).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDC} (1.2 V) supply second.
3. Turn off the V_{DDM} (2.5 V) supply third.
4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDM} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 2 ms for power-up and power-down.
- Refer to **Figure 30** for relative timing for power sequencing case 5.

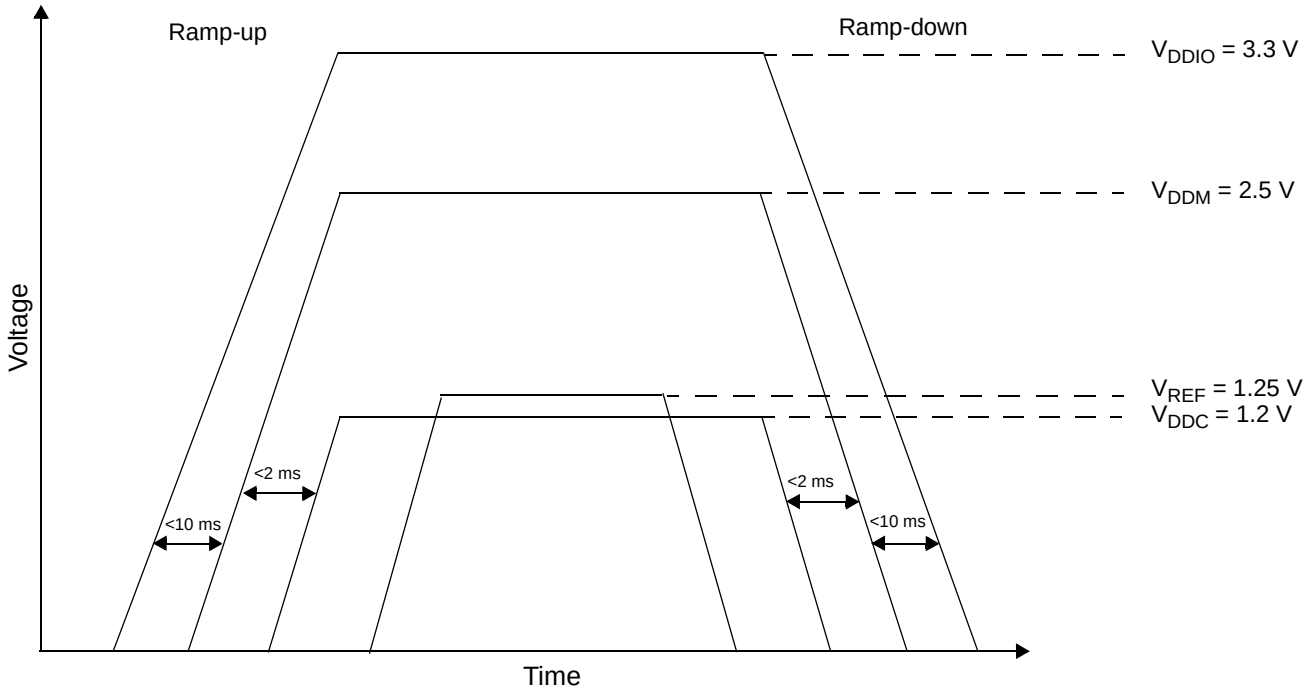

Figure 30. Voltage Sequencing Case 5

Note: Cases 1, 2, 3, and 4 are recommended for system design. Designs that use Case 5 may have large current spikes on the V_{DDM} supply at startup and is not recommended for most designs. If a design uses case 5, it must accommodate the potential current spikes. Verify risks related to current spikes using actual information for the specific application.

3.2.7 Power Supply Design

One of the most common ways to derive power is to use either a simple fixed or adjustable linear regulator. For the system I/O voltage supply, a simple fixed 3.3 V supply can be used. However, a separate adjustable linear regulator supply for the core voltage V_{DDC} should be implemented. For the memory power supply, regulators are available that take care of all DDR power requirements.

Table 30. Recommended Power Supply Ratings

Supply	Symbol	Nominal Voltage	Current Rating
Core	V_{DDC}	1.2 V	1.5 A per device
Memory	V_{DDM}	2.5 V	0.5 A per device
Reference	V_{REF}	1.25 V	10 µA per device
I/O	V_{DDIO}	3.3 V	1.0 A per device

3.3 Estimated Power Usage Calculations

The following equations permit estimated power usage to be calculated for individual design conditions. Overall power is derived by totaling the power used by each of the major subsystems:

$$P_{TOTAL} = P_{CORE} + P_{PERIPHERALS} + P_{DDRIO} + P_{IO} + P_{LEAKAGE} \quad \textit{Eqn. 3}$$

This equation combines dynamic and static power. Dynamic power is determined using the generic equation:

$$C \times V^2 \times F \times 10^{-3}\ mW \quad \textit{Eqn. 4}$$

where,

C = load capacitance in pF

V = peak-to-peak voltage swing in V

F = frequency in MHz

3.3.1 Core Power

Estimation of core power is straightforward. It uses the generic dynamic power equation and assumes that the core load capacitance is 750 pF, core voltage swing is 1.2 V, and the core frequency is 200 MHz or 266 MHz. This yields:

$$P_{CORE} = 750\ pF \times (1.2\ V)^2 \times 200\ MHz \times 10^{-3} = 216\ mW \quad \textit{Eqn. 5}$$

$$P_{CORE} = 750\ pF \times (1.2\ V)^2 \times 266\ MHz \times 10^{-3} = 287\ mW \quad \textit{Eqn. 6}$$

This equation allows for adjustments to voltage and frequency if necessary.

3.4.2 Reset Configuration Pins

Table 31 shows the MSC7112 reset configuration signals. These signals are sampled at the deassertion (rising edge) of PORESET. For details, refer to the Reset chapter of the *MSC711x Reference Manual*.

Table 31. Reset Configuration Signals

Signal	Description	Settings	
BM[1–0]	Determines boot mode.	0	Boot from HDI16 port.
		01	Boot from I2C.
		1x	Reserved.
SWTE	Determines watchdog functionality.	0	Watchdog timer disabled.
		1	Watchdog timer enabled.
HDSP	Configures HDI16 strobe polarity.	0	Host Data strobes active low.
		1	Host Data strobes active high.
H8BIT	Configures HDI16 operation mode.	0	HDI16 port configured for 16-bit operation.
		1	HDI16 port configured for 8-bit operation.

3.4.3 Boot

After a power-on reset, the PLL is bypassed and the device is directly clocked from the CLKIN pin. Using this input clock, the system initializes using the boot loader program that resides in the internal ROM. After initialization, the DSP core can enable the PLL and start the device operating at a higher speed. The MSC7112 can boot from an external host through the HDI16 or download a user program through the I^2C port. The boot operating mode is set by configuring the BM[1–0] signals sampled at the rising edge of PORESET, as shown in **Table 32**.

Table 32. Boot Mode Settings

BM1	BM0	Boot Source
0	0	External host via HDI16 with the PLL disabled.
0	1	I^2C.
1	0	External host via the HDI16 with the PLL enabled.
1	1	Reserved.

3.4.3.1 HDI16 Boot

If the MSC7112 device boots from an external host through the HDI16, the port is configured as follows:

- Operate in Non-DMA mode.
- Operate in polled mode on the device side.
- Operate in polled mode on the external host side.
- External host must write four 16-bit values at a time with the first word as the most significant and the fourth word as the least significant.

When booting from a power-on reset, the HDI16 is additionally configurable as follows:

- 8- or 16-bit mode as specified by the H8BIT pin.
- Data strobe as specified by the HDSP and HDDS pins.

These pins are sampled only on the deassertion of power-on reset. During a boot from a hard reset, the configuration of these pins is unaffected.

Note: When the HDI16 is used for booting or other purposes, bit 0 is the least significant bit and not the most significant bit as for other DSP products.

3.5.3 General Routing

The general routing considerations for the DDR are as follows:

- All DDR signals must be routed next to a solid reference:
  - For data, next to solid ground planes.
  - For address/command, power planes if necessary.
- All DDR signals must be impedance controlled. This is system dependent, but typical values are 50–60 ohm.
- Minimize other cross-talk opportunities. As possible, maintain at least a four times the trace width spacing between all DDR signals to non-DDR signals.
- Keep the number of vias to a minimum to eliminate additional stubs and capacitance.
- Signal group routing priorities are as follows:
  - DDR clocks.
  - Route MVTT/MVREF.
  - Data group.
  - Command/address.
- Minimize data bit jitter by trace matching.

3.5.4 Routing Clock Distribution

The DDR clock distribution considerations are as follows:

- DDR controller supports six clock pairs:
  - 2 DIMM modules.
  - Up to 36 discrete chips.
- For route traces as for any other differential signals:
  - Maintain proper difference pair spacing.
  - Match pair traces within 25 mm.
- Match all clock traces to within 100 mm.
- Keep all clocks equally loaded in the system.
- Route clocks on inner critical layers.

3.5.5 Data Routing

The DDR data routing considerations are as follows:

- Route each data group (8-bits data + DQS + DM) on the same layer. Avoid switching layers within a byte group.
- Take care to match trace lengths, which is extremely important.
- To make trace matching easier, let adjacent groups be routed on alternate critical layers.
- Pin swap bits within a byte group to facilitate routing (discrete case).
- Tight trace matching is recommended within the DDR data group. Keep each 8-bit datum and its DM signal within ± 25 mm of its respective strobe.
- Minimize lengths across the entire DDR channel:
  - Between all groups maintain a delta of no more than 500 mm.
  - Allows greater flexibility in the design for readjustments as needed.
- DDR data group separation:
  - If stack-up allows, keep DDR data groups away from the address and control nets.
  - Route address and control on separate critical layers.
  - If resistor networks (RNs) are used, attempt to keep data and command lines in separate packages.

3.6 Connectivity Guidelines

This section summarizes the connections and special conditions, such as pull-up or pull-down resistors, for the MSC7112 device. Following are guidelines for signal groups and configuration settings:

- *Clock and reset signals*.
  - SWTE is used to configure the MSC7112 device and is sampled on the deassertion of $\overline{\text{PORESET}}$, so it should be tied to V_{DDC} or GND either directly or through pull-up or pull-down resistors until $\overline{\text{PORESET}}$ is deasserted. After $\overline{\text{PORESET}}$, this signal can be left floating.
  - BM[0–1] configure the MSC7112 device and are sampled until $\overline{\text{PORESET}}$ is deasserted, so they should be tied to V_{DDIO} or GND either directly or through pull-up or pull-down resistors.
  - $\overline{\text{HRESET}}$ should be pulled up.
- *Interrupt signals*. When used, $\overline{\text{IRQ}}$ pins must be pulled up.
- *HDI16 signals*.
  - When they are configured for open-drain, the $\overline{\text{HREQ}}$/HREQ or $\overline{\text{HTRQ}}$/HTRQ signals require a pull-up resistor. However, these pins are also sampled at power-on reset to determine the HDI16 boot mode and may need to be pulled down. When these pins must be pulled down on reset and pulled up otherwise, a buffer can be used with the $\overline{\text{HRESET}}$ signal as the enable.
  - When the device boots through the HDI16, the HDDS, HDSP and H8BIT pins should be pulled up or down, depending on the required boot mode settings.
- *I^2C signals*. The SCL and SDA signals, when programmed for I^2C, requires an external pull-up resistor.
- *General-purpose I/O (GPIO) signals*. An unused GPIO pin can be disconnected. After boot, program it as an output pin.
- Other signals.
  - The $\overline{\text{TEST0}}$ pin must be connected to ground.
  - The $\overline{\text{TPSEL}}$ pin should be pulled up to enable debug access via the EOnCE port and pulled down for boundary scan.
  - Pins labelled NO CONNECT (NC) must not be connected.
  - When a 16-pin double data rate (DDR) interface is used, the 16 unused data pins should be no connects (floating) if the used lines are terminated.
  - Do not connect DBREQ to DONE (as you would for the MSC8101 device). Connect DONE to one of the EVNT pins, and DBREQ to HRRQ.

4 Ordering Information

Consult a Freescale Semiconductor sales office or authorized distributor to determine product availability and place an order.

Part	Supply Voltage	Package Type	Pin Count	Core Frequency (MHz)	Solder Spheres	Order Number
MSC7112 (mask 1L44X	1.2 V core 2.5 V mem. 3.3 V I/O	Molded Array Process-Ball Grid Array (MAP-BGA)	400	200	Lead-free	MSC7112VM800
					Lead-bearing	MSC7112VF800
MSC7112 (mask 1M88B)	1.2 V core 2.5 V mem 3.3 V I/O	Molded Array Process-Ball Grid Array (MAP-BGA)	400	266	Lead-free	MSC7112VM1000
					Lead-bearing	MSC7112VF1000

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Japan
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Asia/Pacific:
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+800 2666 8080
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For Literature Requests Only:
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Fax: +1-303-675-2150
LDCForFreescaleSemiconductor
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